

HRW26

Silicon Schottky Barrier Diode for High Frequency Rectifying

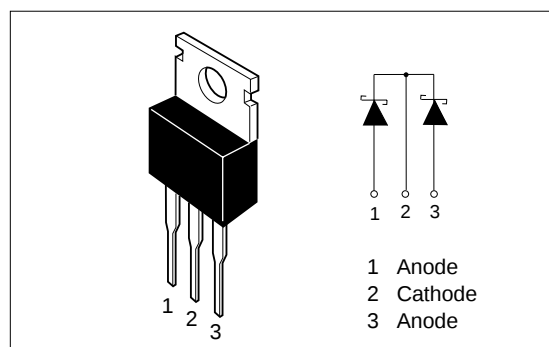
HITACHI

Rev. 2
Nov. 1994**Features**

- Low forward voltage drop. ($V_F = 0.55V$ max)
- High reverse voltage. ($V_R = 40V$ max)

Ordering Information

Type No.	Laser Mark	Package Code
HRW26	HRW26	TO-220AB

Pin Arrangement**Absolute Maximum Ratings** ($T_a = 25^\circ C$) *

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	I_{O}^{**}	10	A
Non-Repetitive peak forward surge current	I_{FSM}^{***}	70	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40 to +125	$^\circ C$

* Per one device

** Square wave, Duty (1/2), $T_c = 95^\circ C$, Sum of two devices

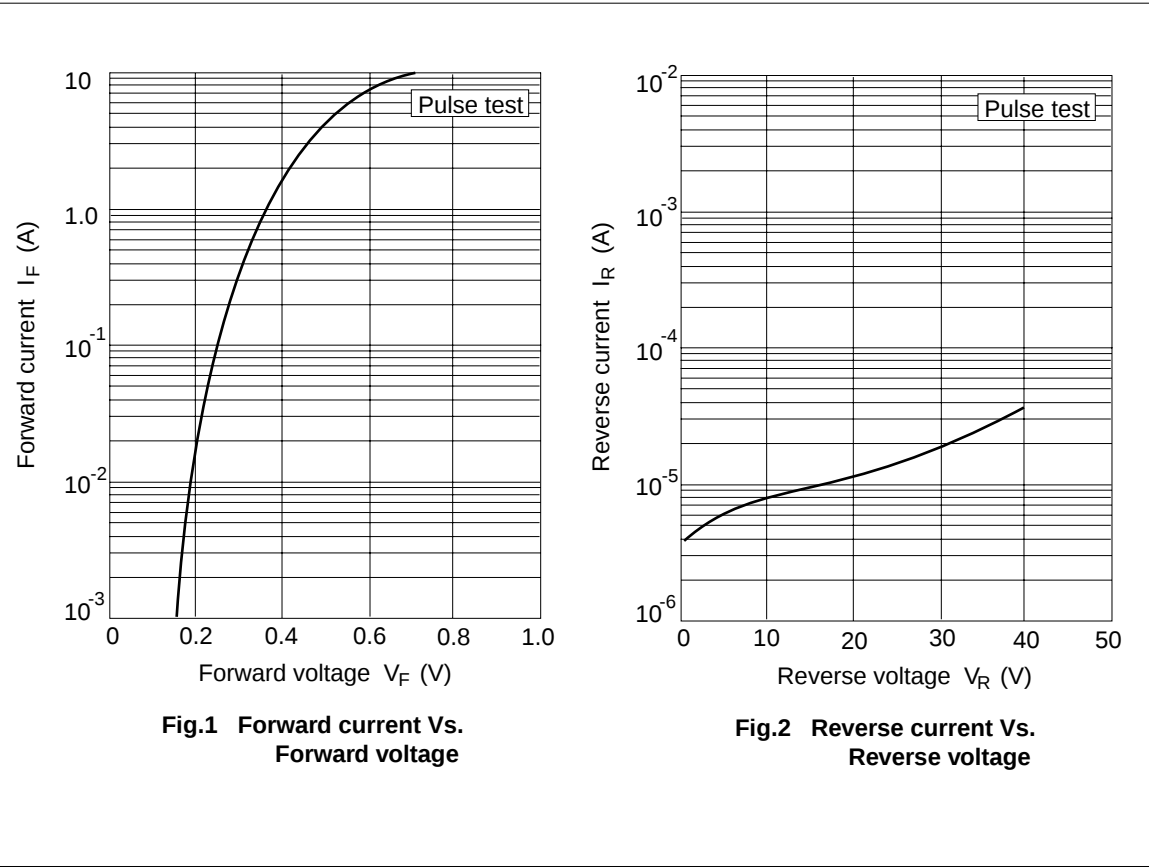
*** Half sine wave 10msec

Electrical Characteristics ($T_a = 25^\circ C$) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.55	V	$I_F = 4.0 A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 40 V$

* Per one device

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Package Dimensions

Unit: mm

